

N- and P-Channel 60-V (D-S) MOSFET

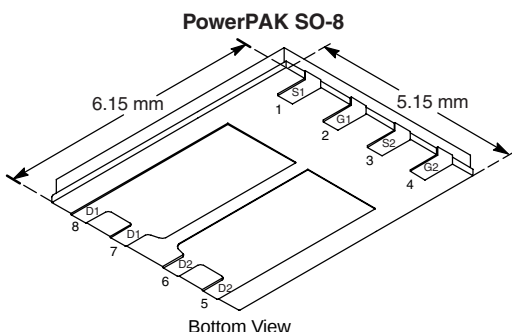
PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
N-Ch	60	0.075 at V _{GS} = 10 V	4.6	12 nC
		0.100 at V _{GS} = 4.5 V	4.0	
P-Ch	- 60	0.064 at V _{GS} = - 10 V	- 5.0	47
		0.080 at V _{GS} = - 4.5 V	- 4.5	

FEATURES

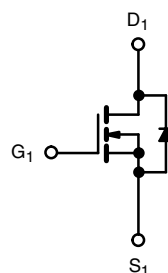
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_g Tested



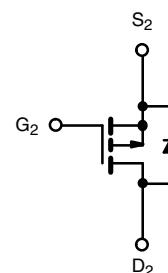
RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si7530DP-T1-E3 (Lead (Pb)-free)
Si7530DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter		Symbol	N-Channel		P-Channel		Unit
			10 s	Steady	10 s	Steady	
Drain-Source Voltage		V _{DS}	60		- 60		V
Gate-Source Voltage		V _{GS}	± 20				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25°C	I _D	4.6	3.0	- 5.0	- 3.2	A
	T _A = 70°C		3.6	2.4	- 4.0	- 2.6	
Pulsed Drain Current		I _{DM}	15		- 25		
Continuous Source Current (Diode Conduction) ^a		I _S	2.7	1.2	- 2.9	- 1.2	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	15		- 22		mJ
Single Pulse Repetitive Avalanche Energy ^b		E _{AS}	11		24.2		
Maximum Power Dissipation ^a	T _A = 25°C	P _D	3.3	1.4	3.5	1.5	W
	T _A = 70°C		2.1	0.9	2.2	0.94	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C
Soldering Recommendations (Peak Temperature) ^{c, d}			260				

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	N-Channel		P-Channel		Unit
		Typical	Maximum	Typical	Maximum	
Maximum Junction-to-Ambient ^a	R _{thJA}	29	38	27	36	°C/W
		60	85	60	85	
Maximum Junction-to-Case (Drain)	R _{thJC}	4.0	5.2	3.3	4.3	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Duty Cycle ≤ 1 %.

c. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ.	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1		3	V
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 1		- 3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	N-Ch P-Ch			± 100 ± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V	P-Ch			- 1	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55°C	N-Ch			5	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55°C	P-Ch			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	15			A
		V _{DS} ≤ - 5 V, V _{GS} = - 10 V	P-Ch	- 25			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 4.6 A	N-Ch		0.060	0.075	Ω
		V _{GS} = - 10 V, I _D = - 5.0 A	P-Ch		0.051	0.064	
		V _{GS} = 4.5 V, I _D = 4.0 A	N-Ch		0.080	0.100	
		V _{GS} = - 4.5 V, I _D = - 4.5 A	P-Ch		0.064	0.080	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 4.6 A	N-Ch		6		S
		V _{DS} = - 15 V, I _D = - 5.0 A	P-Ch		16		
Diode Forward Voltage ^a	V _{SD}	I _S = 2.7 A, V _{GS} = 0 V	N-Ch		0.85	1.2	V
		I _S = - 2.9 A, V _{GS} = 0 V	P-Ch		- 0.85	- 1.2	
Dynamic ^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 30 V, V _{GS} = 10 V, I _D = 15 A	N-Ch P-Ch		12 26	20 40	nC
Gate-Source Charge	Q _{gs}		N-Ch P-Ch		2 4.5		
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 5.0 A	N-Ch P-Ch		3.5 7		
Gate Resistance	R _g	f = 1.0 MHz	N-Ch P-Ch	0.6 3.5	1.5 7	2.5 11	Ω
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 30 V, R _L = 30 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω	N-Ch P-Ch		7 8	15 15	ns
Rise Time	t _r		N-Ch P-Ch		8 9	15 15	
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 30 V, R _L = 30 Ω I _D ≅ - 1 A, V _{GEN} = - 10 V, R _g = 6 Ω	N-Ch P-Ch		15 65	25 100	
Fall Time	t _f		N-Ch P-Ch		7 30	20 45	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.7 A, dI/dt = 100 A/μs	N-Ch		30	60	
		I _F = - 5 A, dI/dt = 100 A/μs	P-Ch		40	80	
Reverse Recovery Energy	Q _{rr}	I _F = 2.7 A, dI/dt = 100 A/μs	N-Ch		33	66	pC
		I _F = - 5 A, dI/dt = 100 A/μs	P-Ch		57	115	

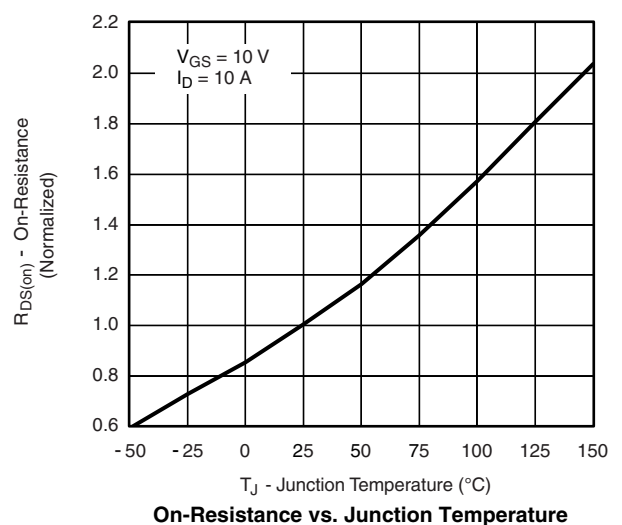
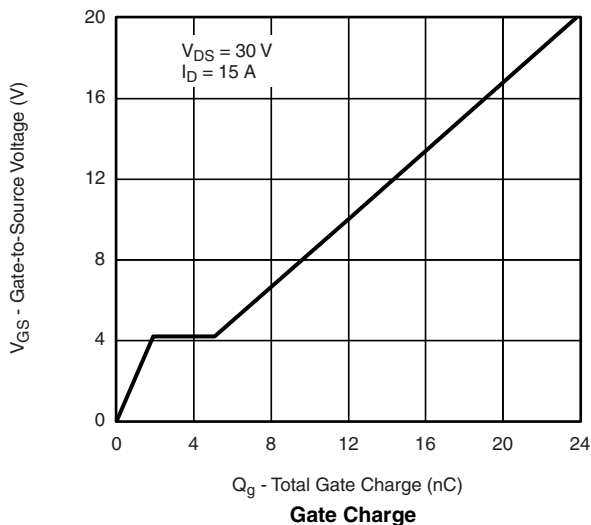
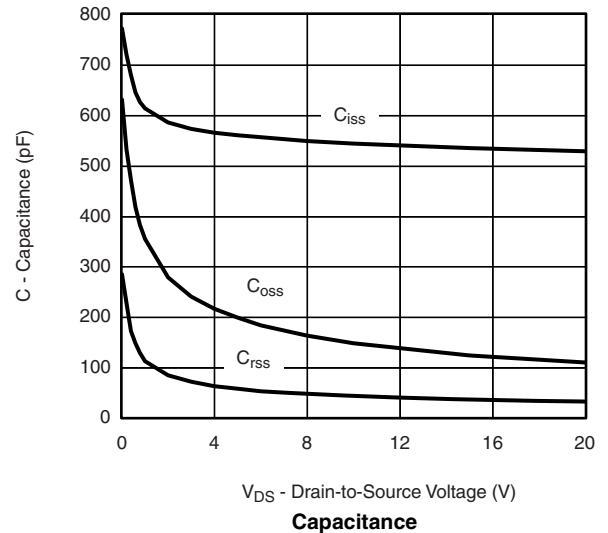
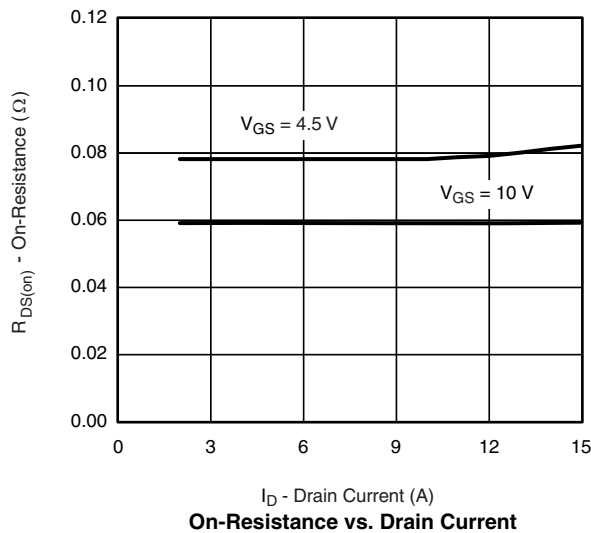
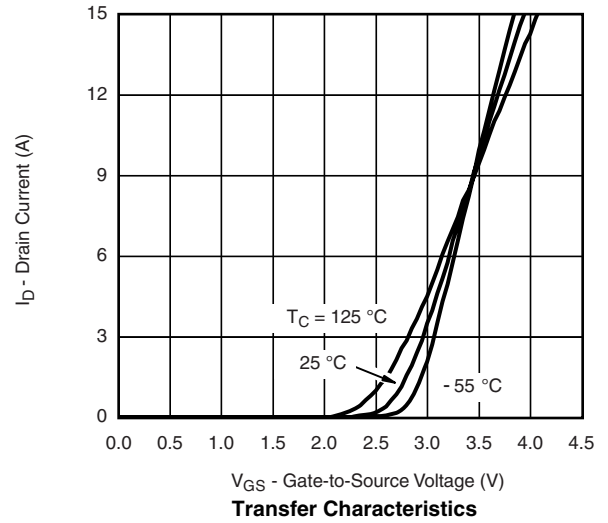
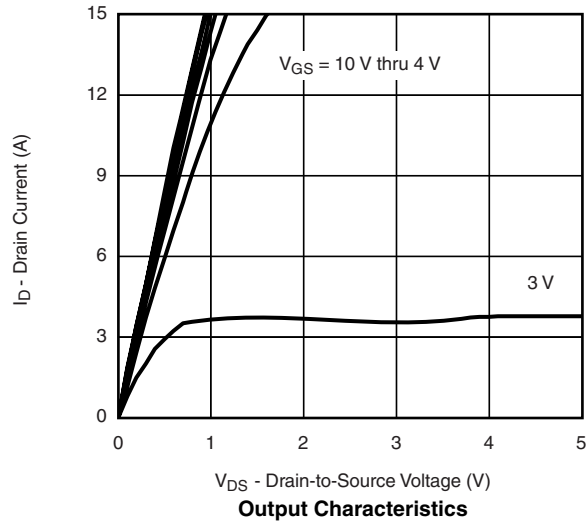
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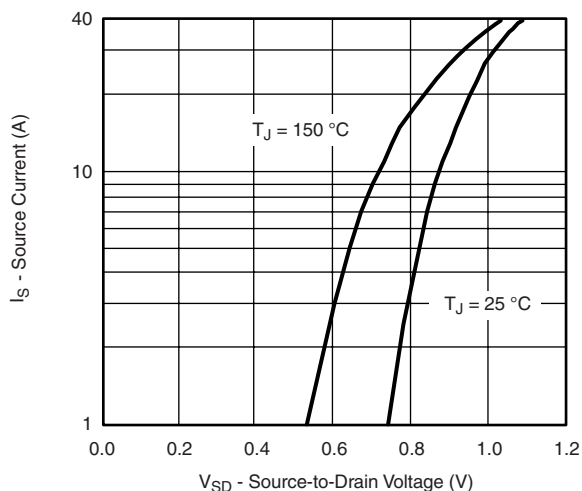
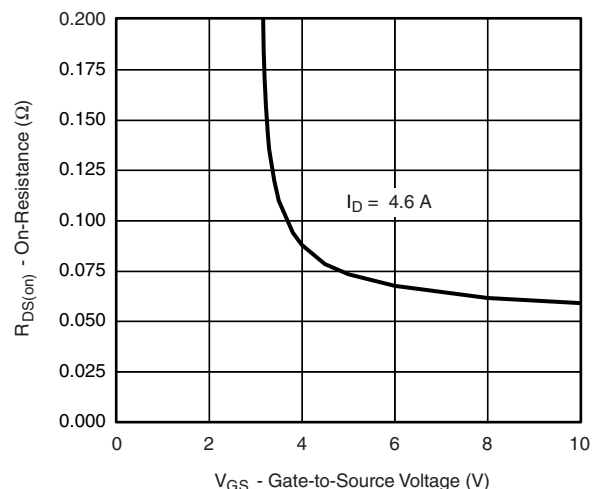
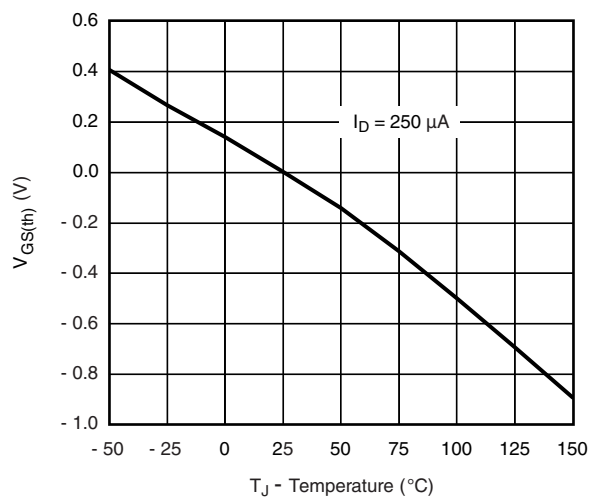
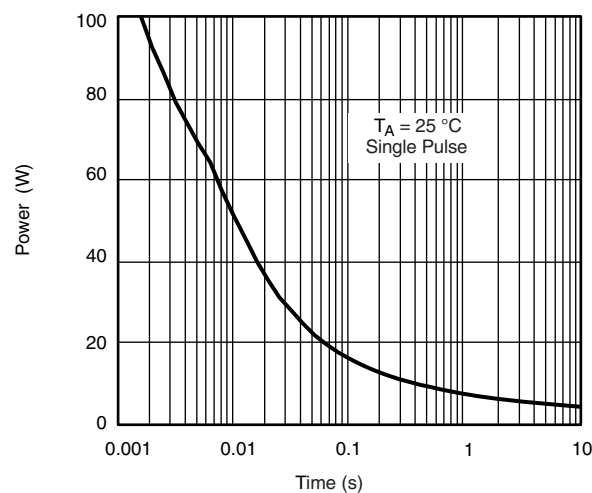
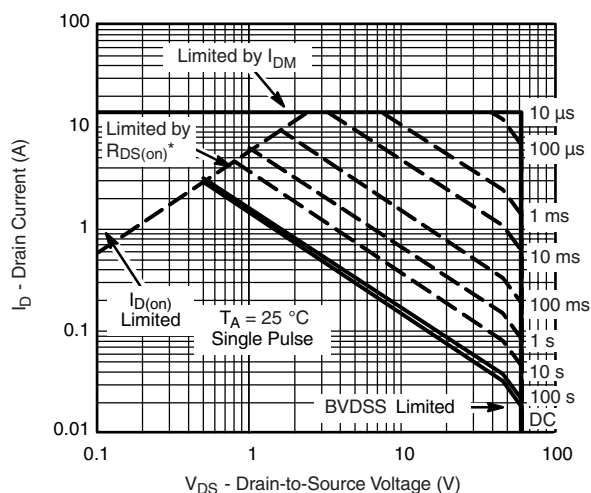
a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

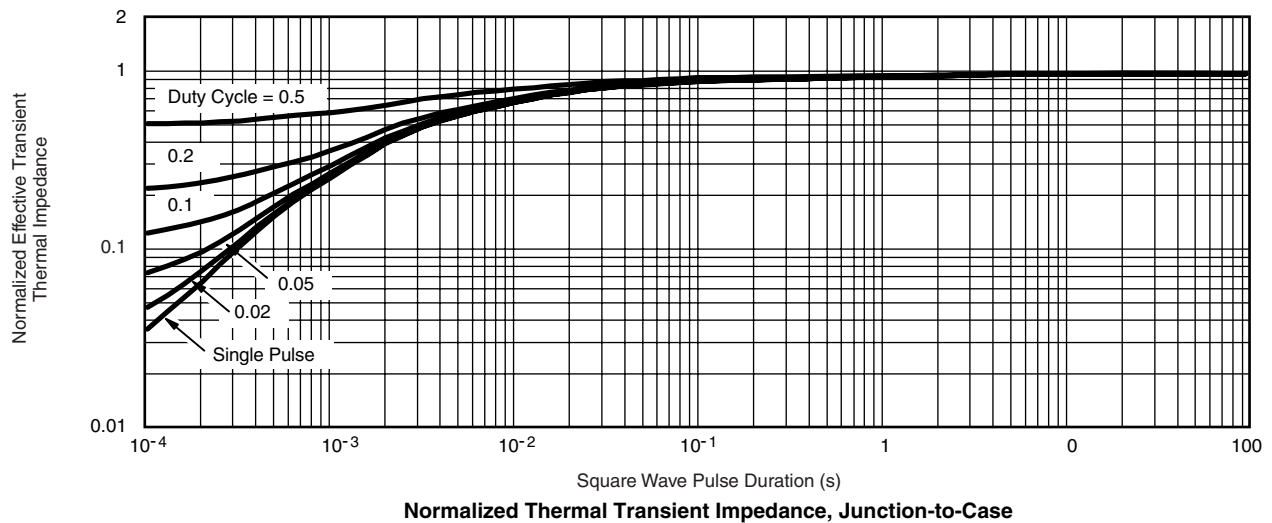
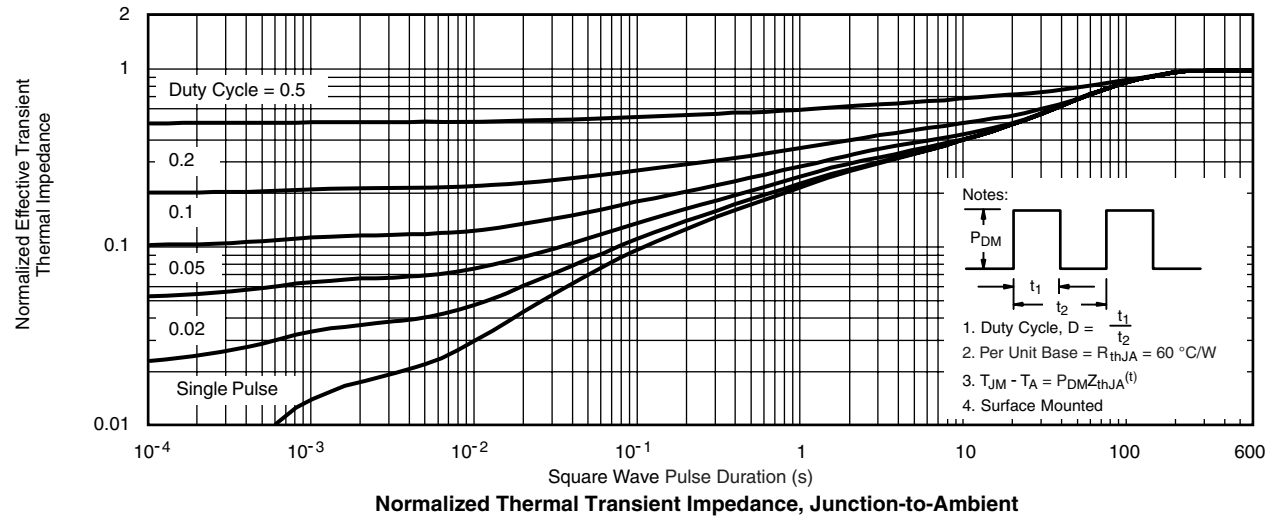
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

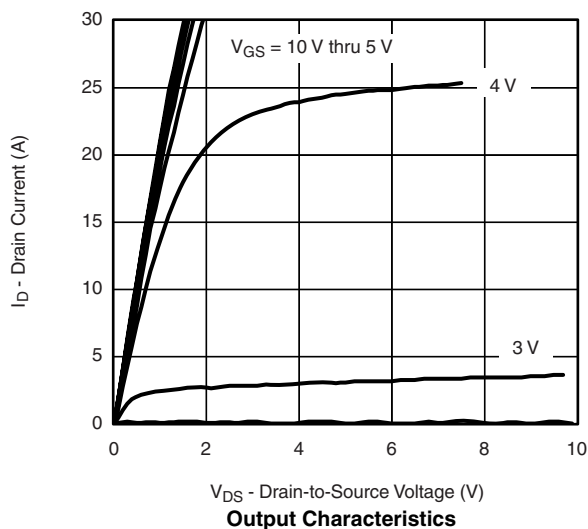
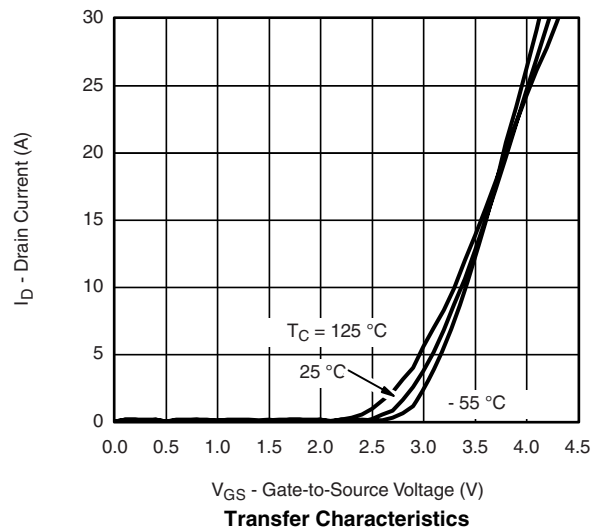
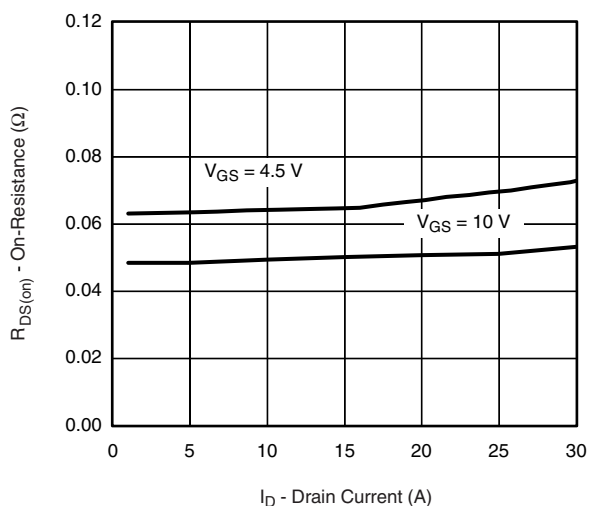
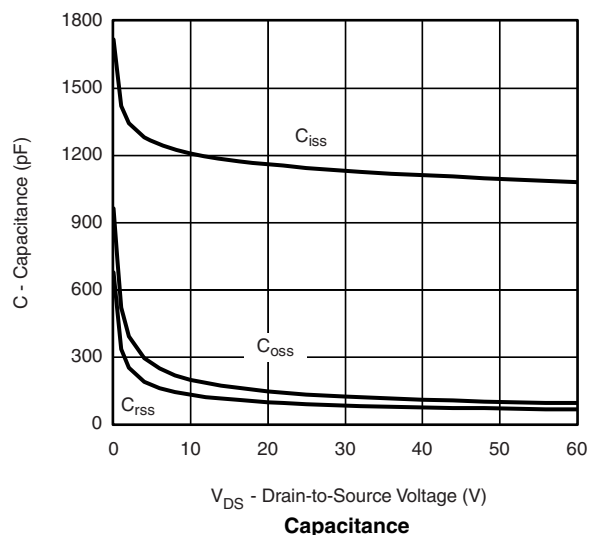
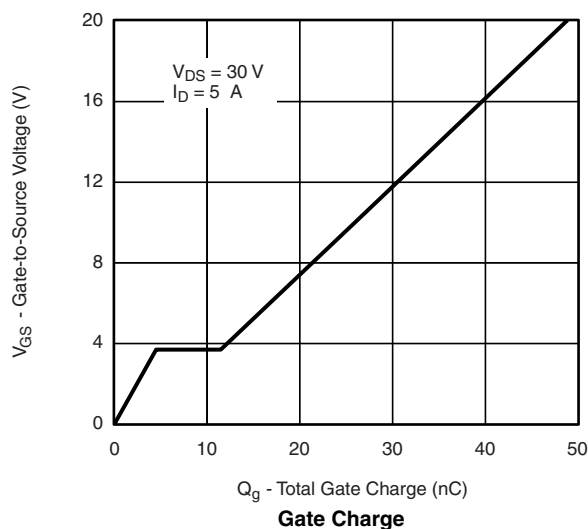
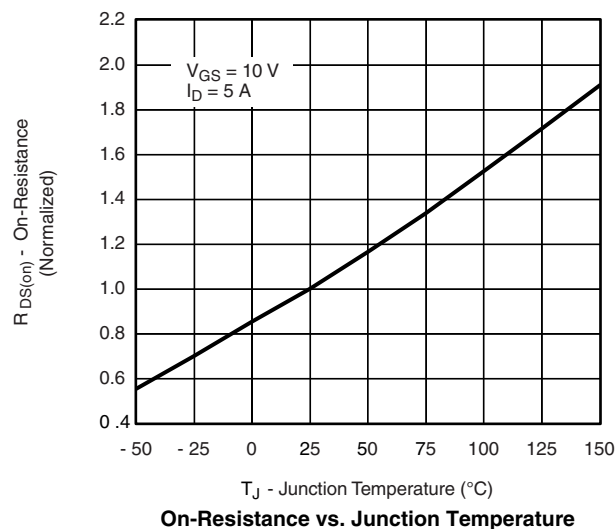
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



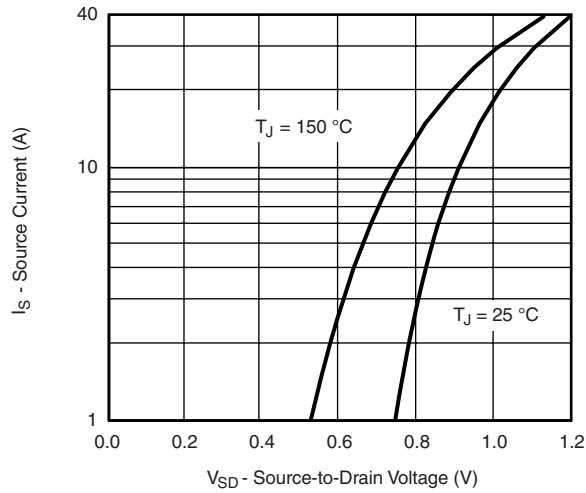
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Case**

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

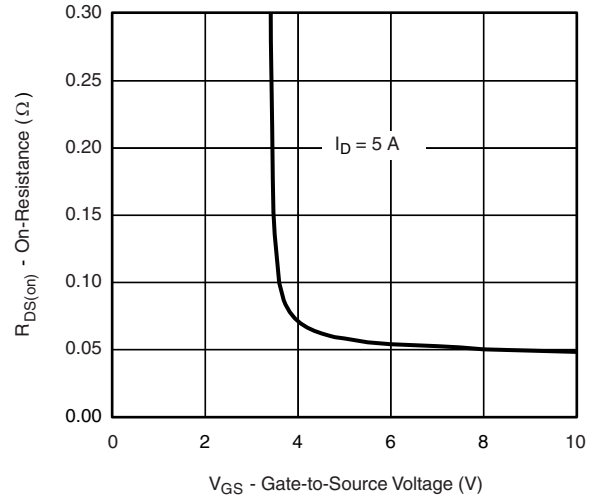


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

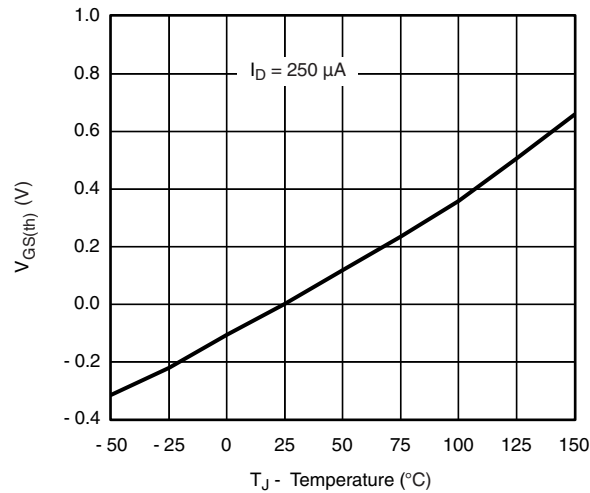
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



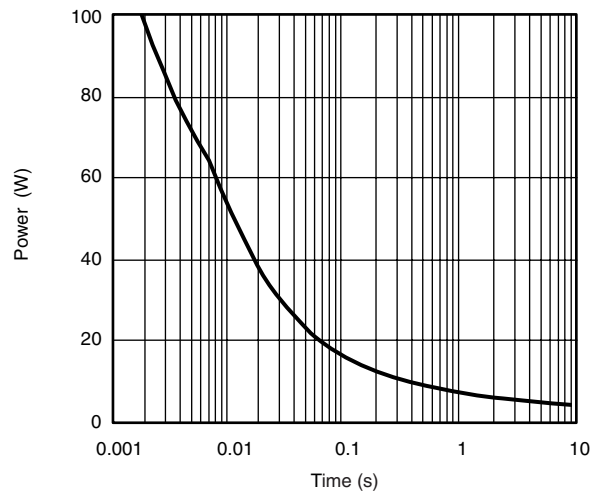
Source-Drain Diode Forward Voltage



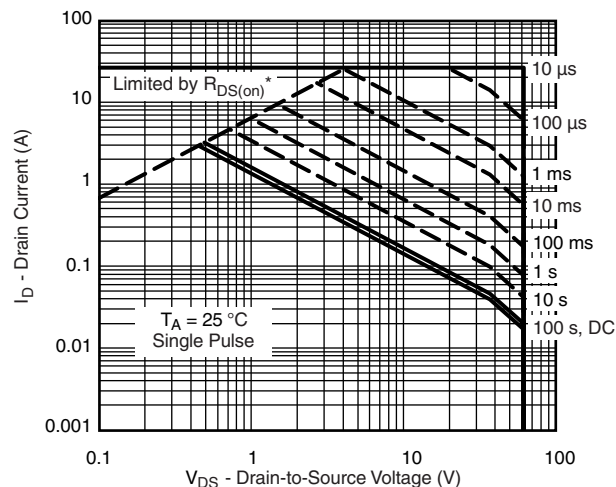
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

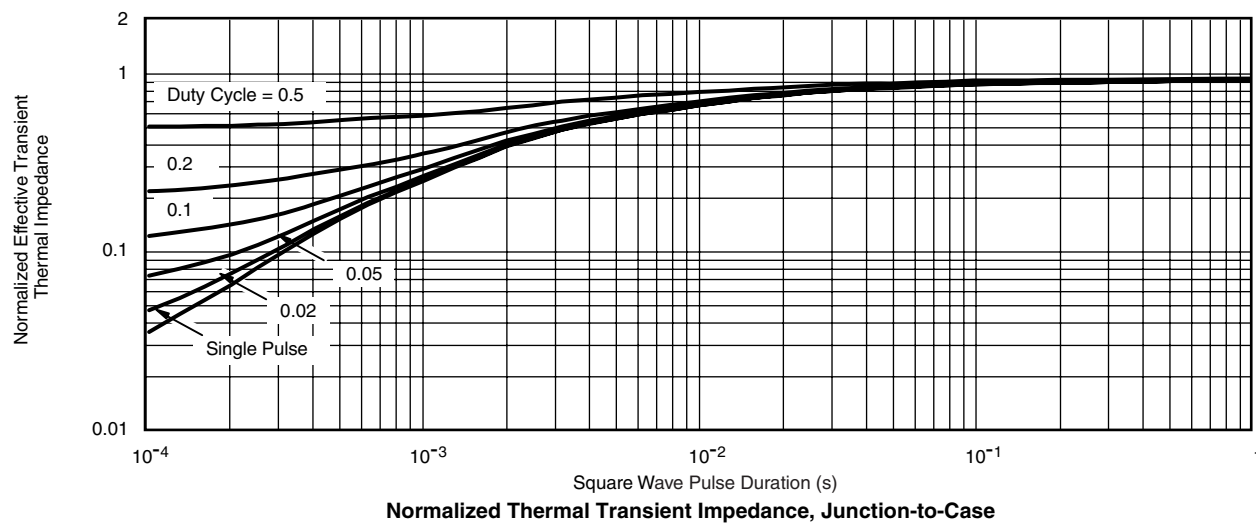
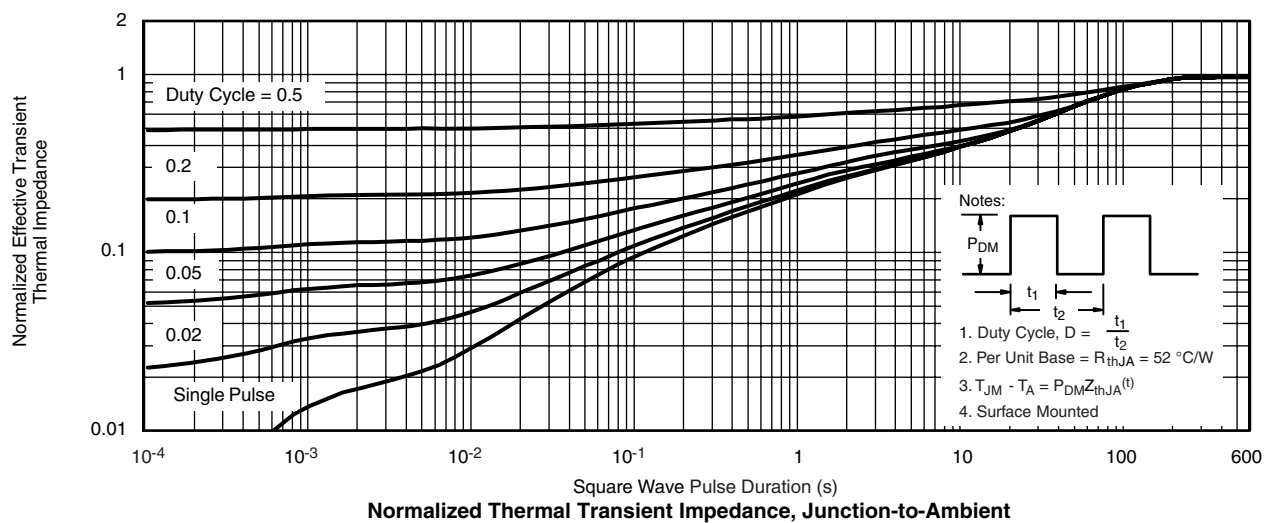


Single Pulse Power, Junction-to-Ambient



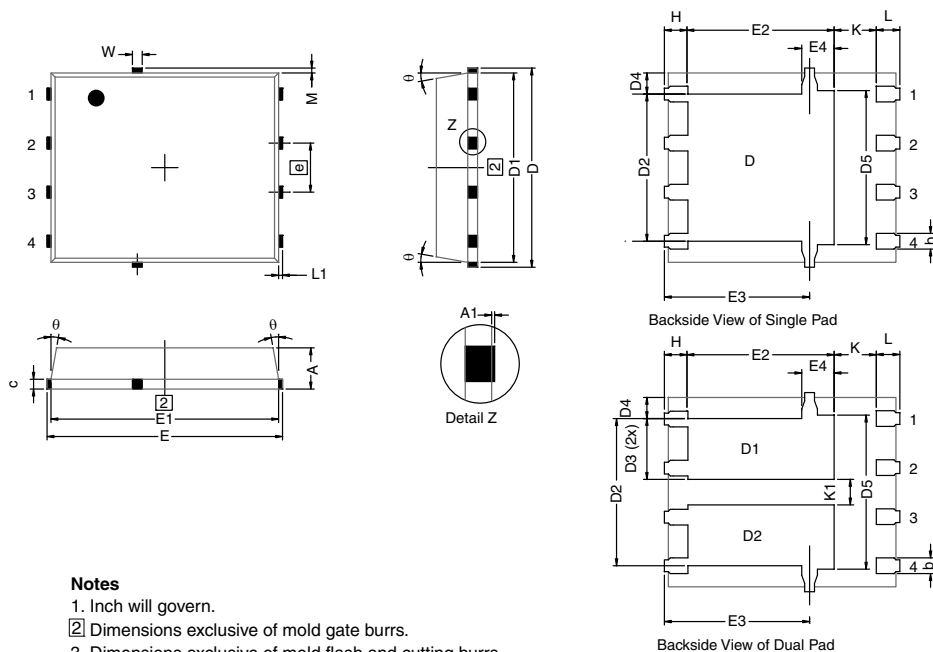
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

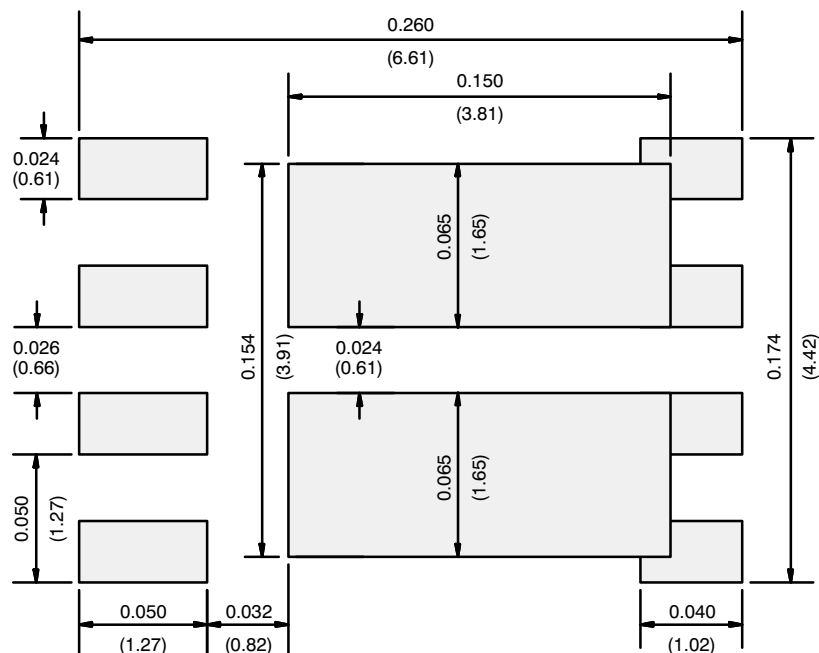
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PowerPAK® SO-8, (Single/Dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4	0.57 typ.			0.0225 typ.		
D5	3.98 typ.			0.157 typ.		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4 (for AL product)	0.58 typ.			0.023 typ.		
E4 (for other product)	0.75 typ.			0.030 typ.		
e	1.27 BSC			0.050 BSC		
K (for AL product)	1.45 typ.			0.057 typ.		
K (for other product)	1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		
ECN: C13-0702-Rev. K, 20-May-13						
DWG: 5881						

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Dual



Recommended Minimum Pads
Dimensions in Inches/(mm)

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